

2304

4.0 Watts - 20 Volts, Class C Microwave 2300 MHz

GENERAL DESCRIPTION

The 2304 is a COMMON BASE transistor capable of providing 4 Watts Class C, RF output power at 2300 MHz. Gold metalization and diffused ballasting are used to provide high reliability and supreme ruggedness. The transistor uses a fully hermetic High Temperature Solder Sealed package.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C 10.2 Watts

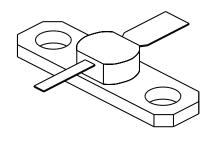
Maximum Voltage and Current

BVces Collector to Emitter Voltage 45 Volts
BVebo Emitter to Base Voltage 3.5 Volts
Ic Collector Current 0.6 A

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 200^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$

CASE OUTLINE 55 BT- Style 1



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	F = 2.3 GHz Vcb = 20 Volts Po = 4 Watts As Above F = 2.3 GHz, Po = 4 W	4.0 8.0	40	0.63	Watt Watt dB %

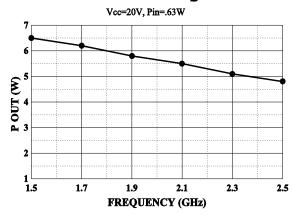
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Volts mA pF °C/W	1.5	7.0	3.5	,	Output Capacitance	Cob
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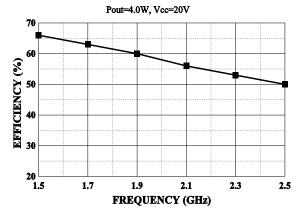
GHz TECHNOLOGY INC. RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE. GHZ RECOMMENDS THAT BEFORE THE PRODUCT(S) DESCRIBED HEREIN ARE WRITTEN INTO SPECIFICATIONS, OR USED IN CRITICAL APPLICATIONS, THAT THE PERFORMANCE CHARACTERISTICS BE VERIFIED BY CONTACTING THE FACTORY.



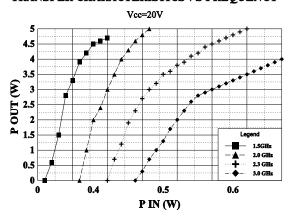
POWER OUTPUT VS FREQUENCY



EFFICIENCY VS FREQUENCY



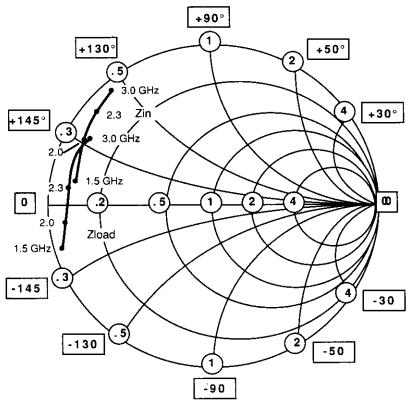
TRANSFER CHARACTERISTICS VS FREQUENCY



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SMITH CHART

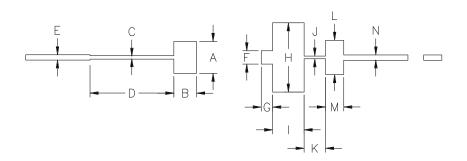
NORMALIZED IMPEDANCE AND ADMITTANCE COORDINATES



NORMALIZED TO A 50 OHM SYSTEM.

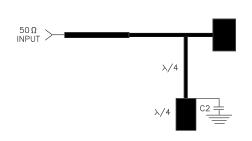
FREQUENCY MHz	R Zi	n JX	FREQUENCY MHz	Zloa R	ad JX
1500	4	5	1500	3.9	16
2000	3.3	15	2000	2.7	3
2300	3.0	18	2300	2.6	-3
3000	2.5	2 2	3000	1.8	-7.5

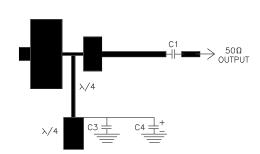
		V		
REVISIONS				
ZONE	REV	DESCRIPTION	DATE	APPROVED



DIM	INCHES		
Α	.350		
В	.250		
С	.038		
D	.920		
Ε	.058		
F	.145		
G	.125		
Н	.760		
1	.345		
J	.030		
K	.235		
L	.375		
М	.200		
N	.058		

2304 TEST CIRCUIT F = 2.3 GHz





= Microstrip on 0.010" Duroid, Er=2.3 C1,C2 = 100PF ATC "A" C3 = 82PF ATC "B" C4 = 10MFD 35v



cage OPJR2	DWG NO.	2304		
	SCALE	1/1	SHEET	